# N-Channel 100-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed

## **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
100	26 @ V <sub>GS</sub> = 10V	9.5		
	36 @ V <sub>GS</sub> = 4.5V	8.1		

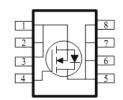




RoHS

COMPLIANT

HALOGEN



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			100	V		
Gate-Source Voltage	V <sub>GS</sub>	±20	V			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I <sub>D</sub>	9.5	А		
	T <sub>A</sub> =70°C		7.2			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	40			
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>s</sub>	4.8	А		
Power Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.5	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	'D	2	٧V		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	- R <sub>θJA</sub>	35	°C/W		
	Steady State		81			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

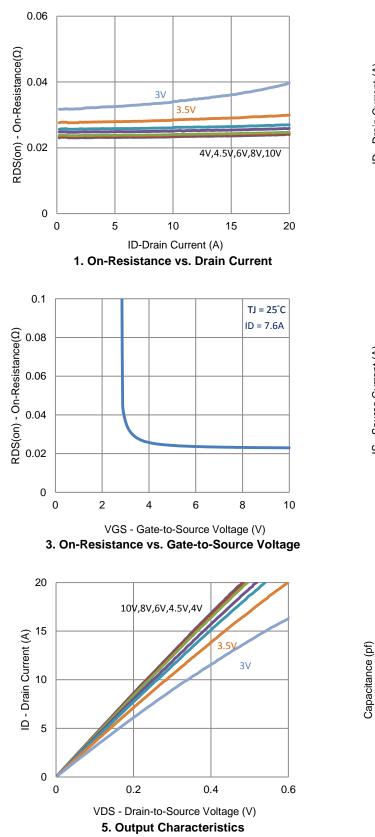
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	15			А	
Drain Source On Desistence a	r.	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.6 A			26	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.3 \text{ A}$			36	111(2	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 7.8 \text{ A}$		31		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.4 \text{ A}, V_{GS} = 0 \text{ V}$		0.76		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 4.5 V,		30			
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS} = 30  V,  V_{\rm GS} = 4.3  V,$ $I_{\rm D} = 7.6  {\rm A}$		11		nC	
Gate-Drain Charge	$Q_gd$	1 <u>0</u> - 7.0 A		10			
Turn-On Delay Time	t <sub>d(on)</sub>			10			
Rise Time	t <sub>r</sub>	$V_{DS}$ = 50 V, $R_L$ = 6.6 $\Omega$ , $I_D$ = 7.6 A,		20		nc	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		90		ns	
Fall Time	t <sub>f</sub>			25			
Input Capacitance	C <sub>iss</sub>			3994			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ Mhz}$		161		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			135			

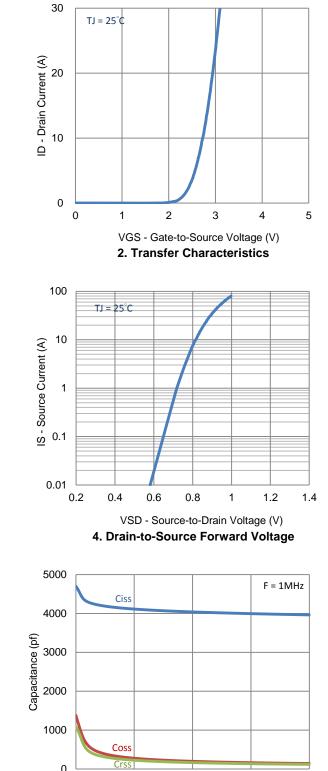
#### Notes

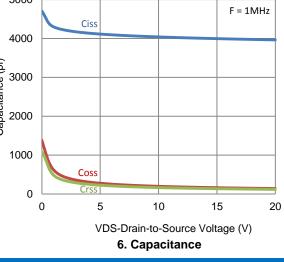
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

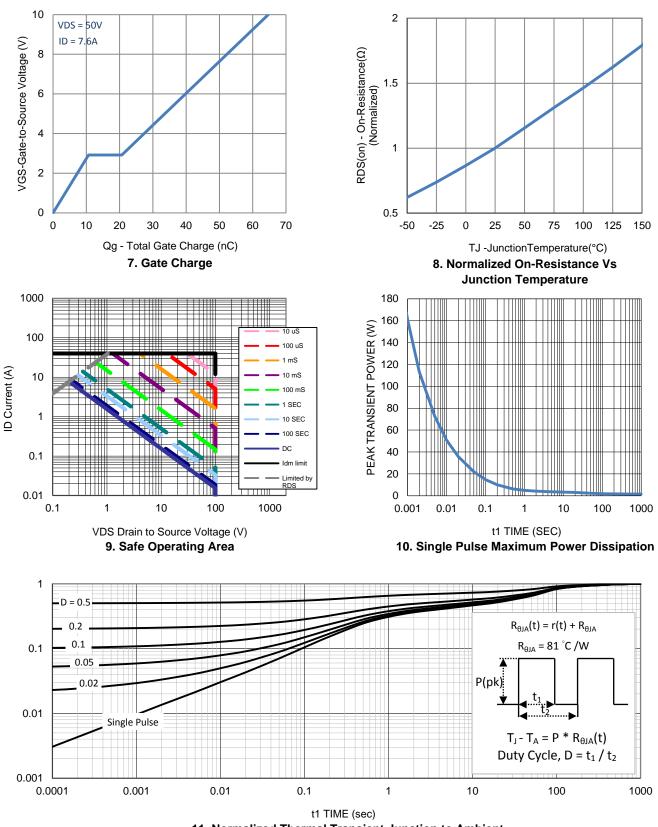
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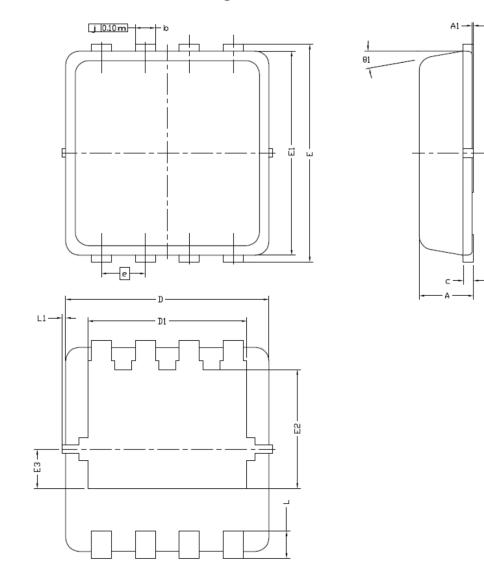




## **Typical Electrical Characteristics**

11. Normalized Thermal Transient Junction to Ambient

# Package Information



птм	MILLIMETERS			INCHES			
DIM,	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0.0315	0.0354	
A1	0,00		0,05	0.000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
С	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.35 BSC			0.093 BSC			
Ε	3.20 BSC			0.126 BSC			
E1	3.00 BSC			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
e	0	0.65 BSC			0,026 BSC		
L	0,30	0,40	0,50	0,0118	0.0157	0.0197	
L1	0		0,100	0		0.004	
01	۰0	10°	12°	0°	10°	12°	